CE3110 - Electronic Devices Laboratory

CE 3110 Electronic Devices Laboratory (1 semester credit hour) Laboratory to accompany CE 3310. Experimental determination and illustration of properties of carriers in semiconductors including carrier drift, carrier diffusion; p-n junctions including forward and reverse bias effects and transient effects; bipolar transistors including the Ebers-Moll model and secondary effects; field effect transistors including biasing effects, MOS capacitance and threshold voltage. Corequisite: CE 3310 or EE 3310. Prerequisite: RHE T 1302. (Same as EE 3110) (0-3) S